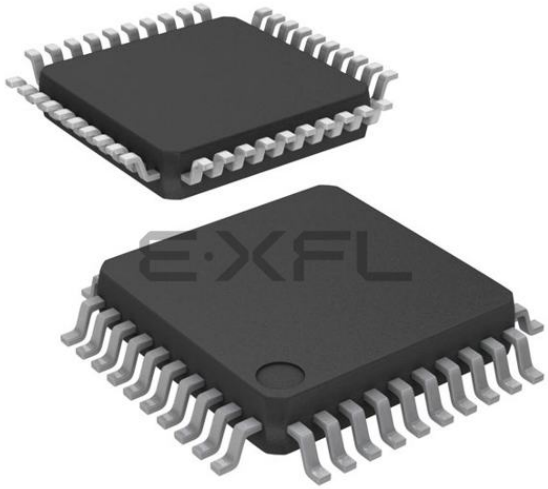

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21274jfp-u0

Table 1.4 Product Information for R8C/27 Group Current of Sep. 2008

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F21272SNFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	
R5F21274SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SNXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	Factory programming product(1)
R5F21274SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		

NOTE:
1. The user ROM is programmed before shipment.

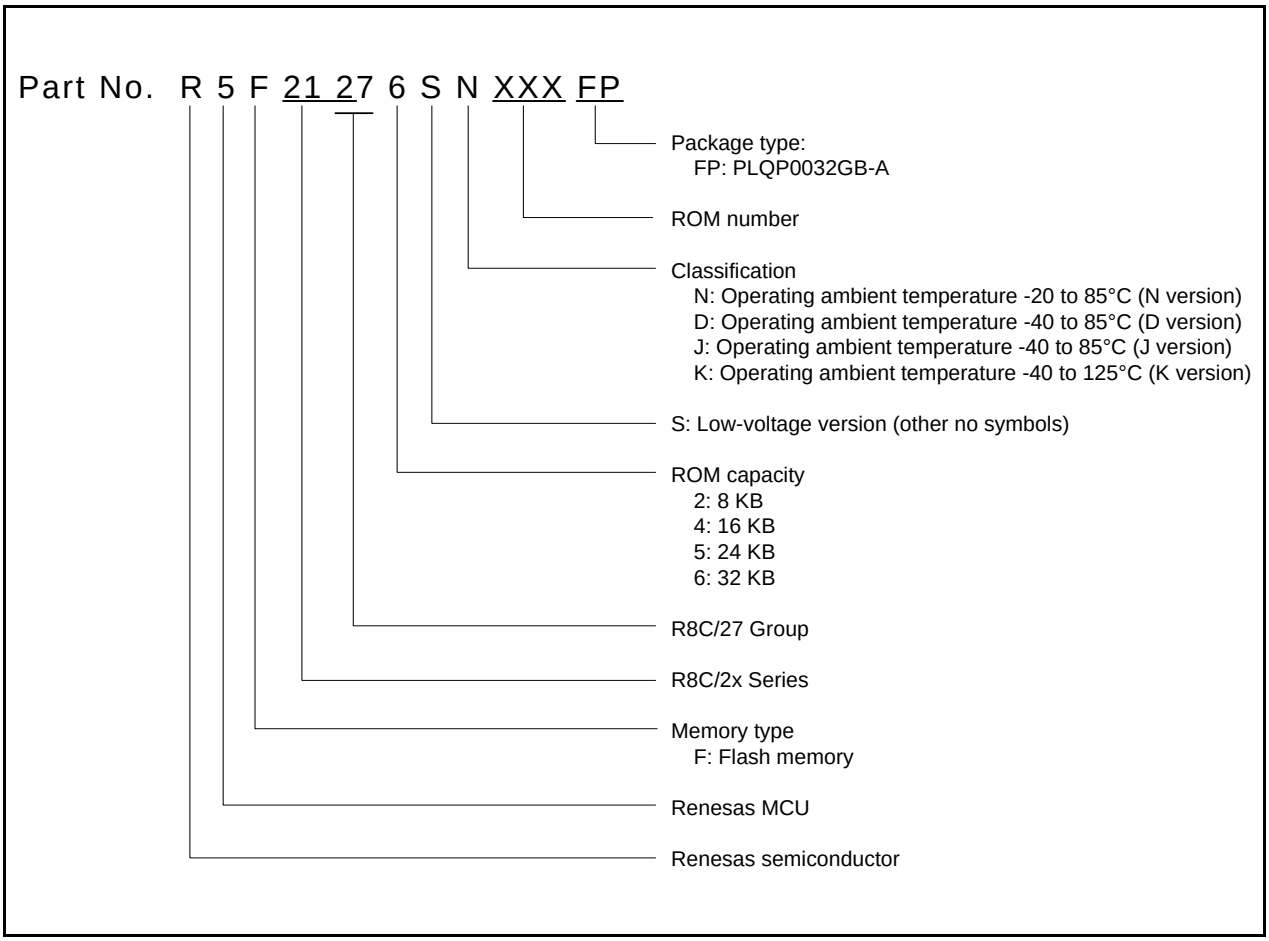
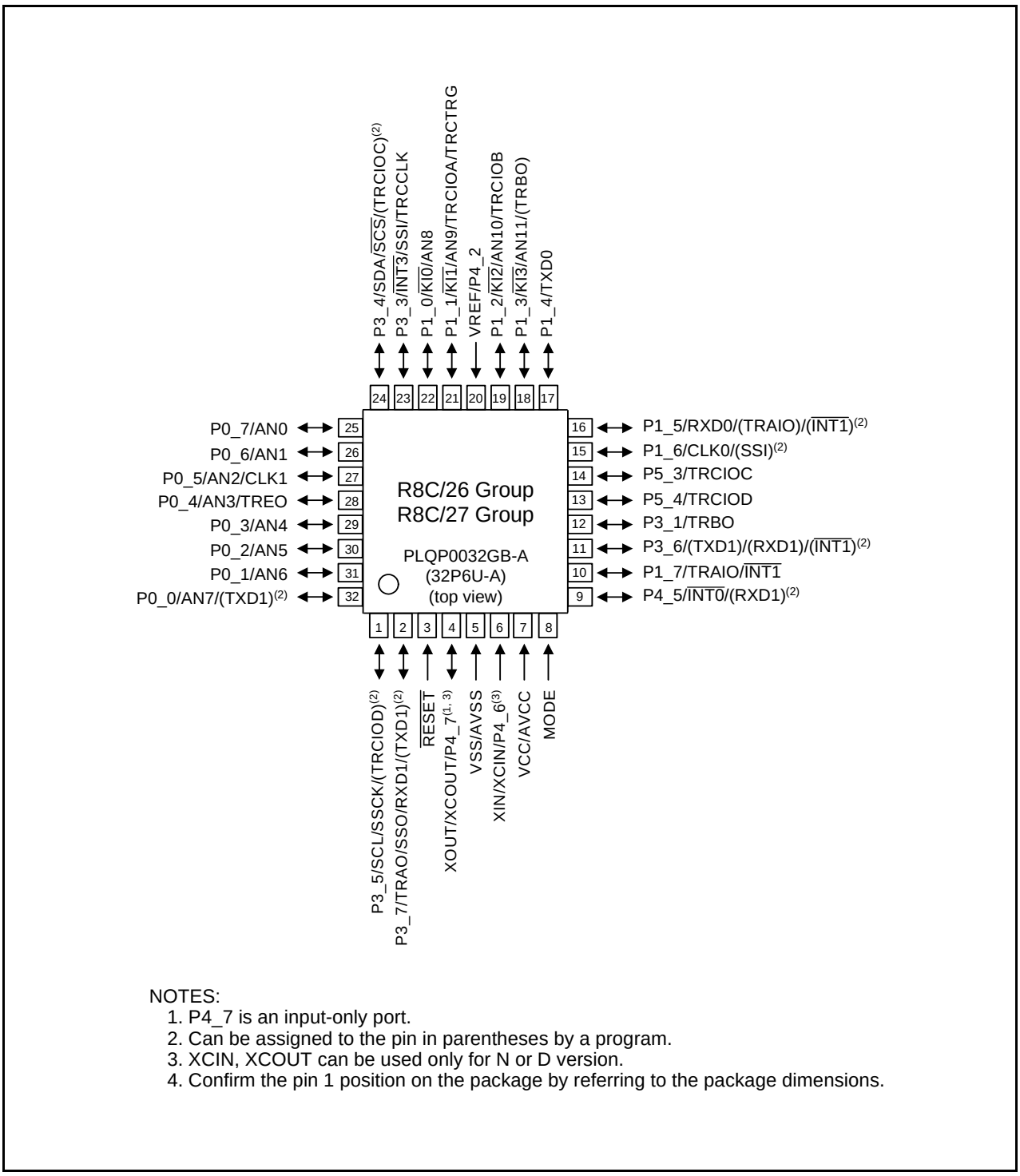


Figure 1.3 Part Number, Memory Size, and Package of R8C/27 Group

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments (Top View).

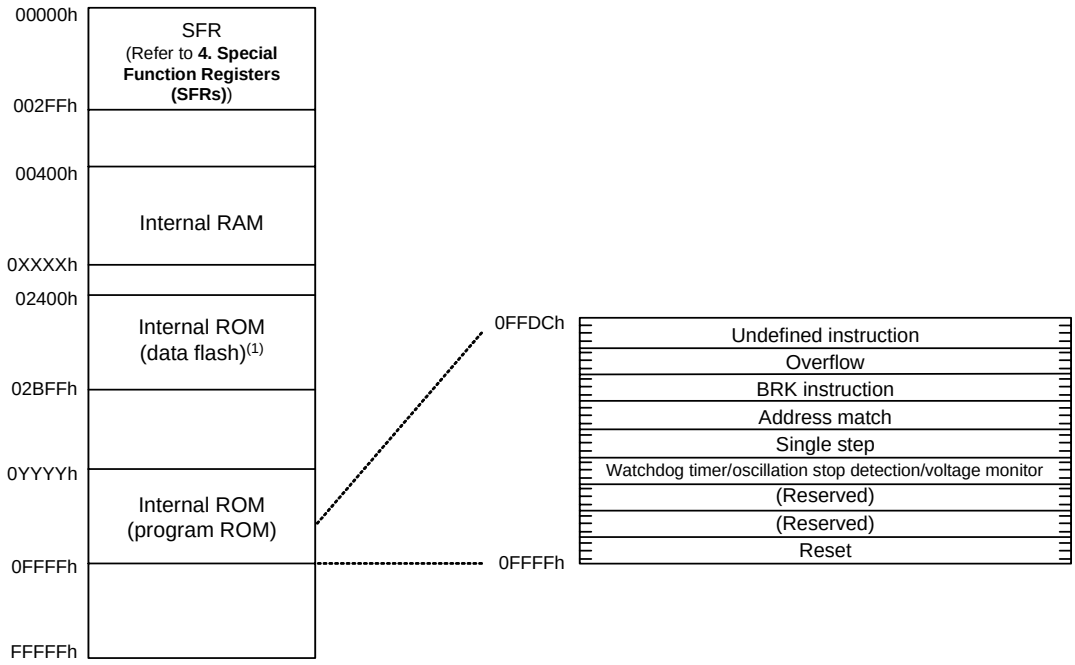


NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. XCIN, XCOUT can be used only for N or D version.
4. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

3.2 R8C/27 Group

Figure 3.2 is a Memory Map of R8C/27 Group. The R8C/27 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21272SNFP, R5F21272SDFP, R5F21272SNXXXFP, R5F21272SDXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21274SNFP, R5F21274SDFP, R5F21274JFP, R5F21274KFP, R5F21274SNXXXFP, R5F21274SDXXXFP, R5F21274JXXXFP, R5F21274KXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21275SNFP, R5F21275SDFP, R5F21275SNXXXFP, R5F21275SDXXXFP	24 Kbytes	0A000h	1.5 Kbytes	009FFh
R5F21276SNFP, R5F21276SDFP, R5F21276JFP, R5F21276KFP, R5F21276SNXXXFP, R5F21276SDXXXFP, R5F21276JXXXFP, R5F21276KXXXFP	32 Kbytes	08000h	1.5 Kbytes	009FFh

Figure 3.2 Memory Map of R8C/27 Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.7 list the special function registers.

Table 4.1 SFR Information (1)[1]

Address	Register	Symbol	After reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	01101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h			
0009h			
000Ah	Protect Register	PRCR	00h
000Bh			
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00X11111b
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			00h
0013h	Address Match Interrupt Enable Register	AIER	00h
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			00h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b[2]
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h			
0027h			
0028h	Clock Prescaler Reset Flag	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4[3]	FRA4	When shipping
002Ah			
002Bh	High-Speed On-Chip Oscillator Control Register 6[3]	FRA6	When shipping
002Ch	High-Speed On-Chip Oscillator Control Register 7[3]	FRA7	When shipping
002Dh			
002Eh			
002Fh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The CSPROINI bit in the OFS register is set to 0.
3. In J, K version these regions are reserved. Do not access locations in these regions.

Table 4.4 SFR Information (4)[1]

Address	Register	Symbol	After reset
00C0h	A/D Register	AD	XXh
00C1h			XXh
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Control Register 2	ADCON2	00h
00D5h			
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h			
00D9h			
00DAh			
00DBh			
00DCh			
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	00h
00E1h	Port P1 Register	P1	00h
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h			
00E5h	Port P3 Register	P3	00h
00E6h			
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	00h
00E9h	Port P5 Register	P5	00h
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh			
00EDh			
00EEh			
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h	Pin Select Register 1	PINSR1	00h
00F6h	Pin Select Register 2	PINSR2	00h
00F7h	Pin Select Register 3	PINSR3	00h
00F8h	Port Mode Register	PMR	00h
00F9h	External Input Enable Register	INTEN	00h
00FAh	INT Input Filter Select Register	INTF	00h
00FBh	Key Input Enable Register	KIEN	00h
00FCh	Pull-Up Control Register 0	PUR0	00h
00FDh	Pull-Up Control Register 1	PUR1	00h
00FEh	Port P1 Drive Capacity Control Register[2]	P1DRR	00h
00FFh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. In J, K version these regions are reserved. Do not access locations in these regions.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/26 Group	100(3)	–	–	times
		R8C/27 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

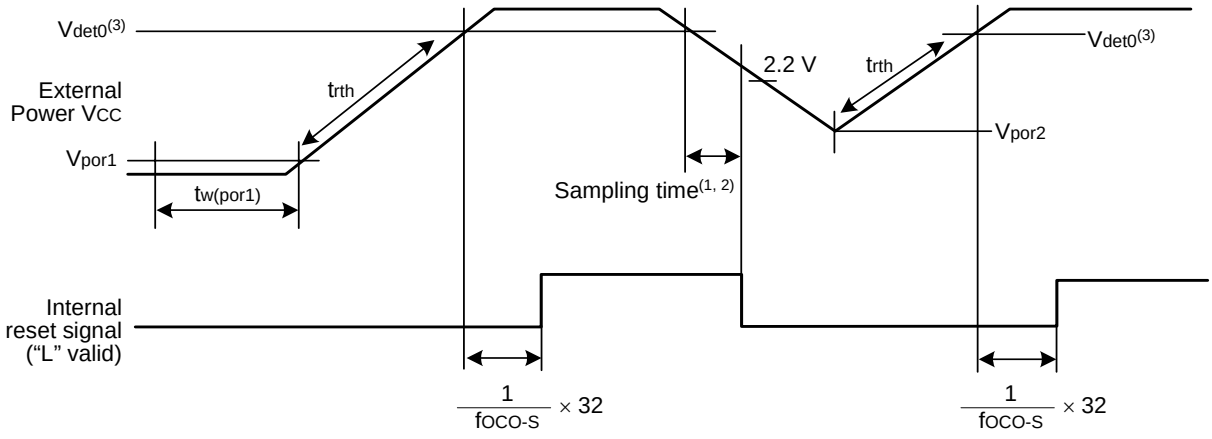
Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.9 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V_{det0}	V
t_{rth}	External power V_{CC} rise gradient(2)		20	–	–	mV/msec

NOTES:
1. The measurement condition is T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if $V_{CC} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if -20°C ≤ T_{opr} ≤ 85°C, maintain $t_{w(por1)}$ for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.



NOTES:
1. When using the voltage monitor 0 digital filter, ensure that the voltage is within the MCU operation voltage range (2.2 V or above) during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.3 Reset Circuit Electrical Characteristics

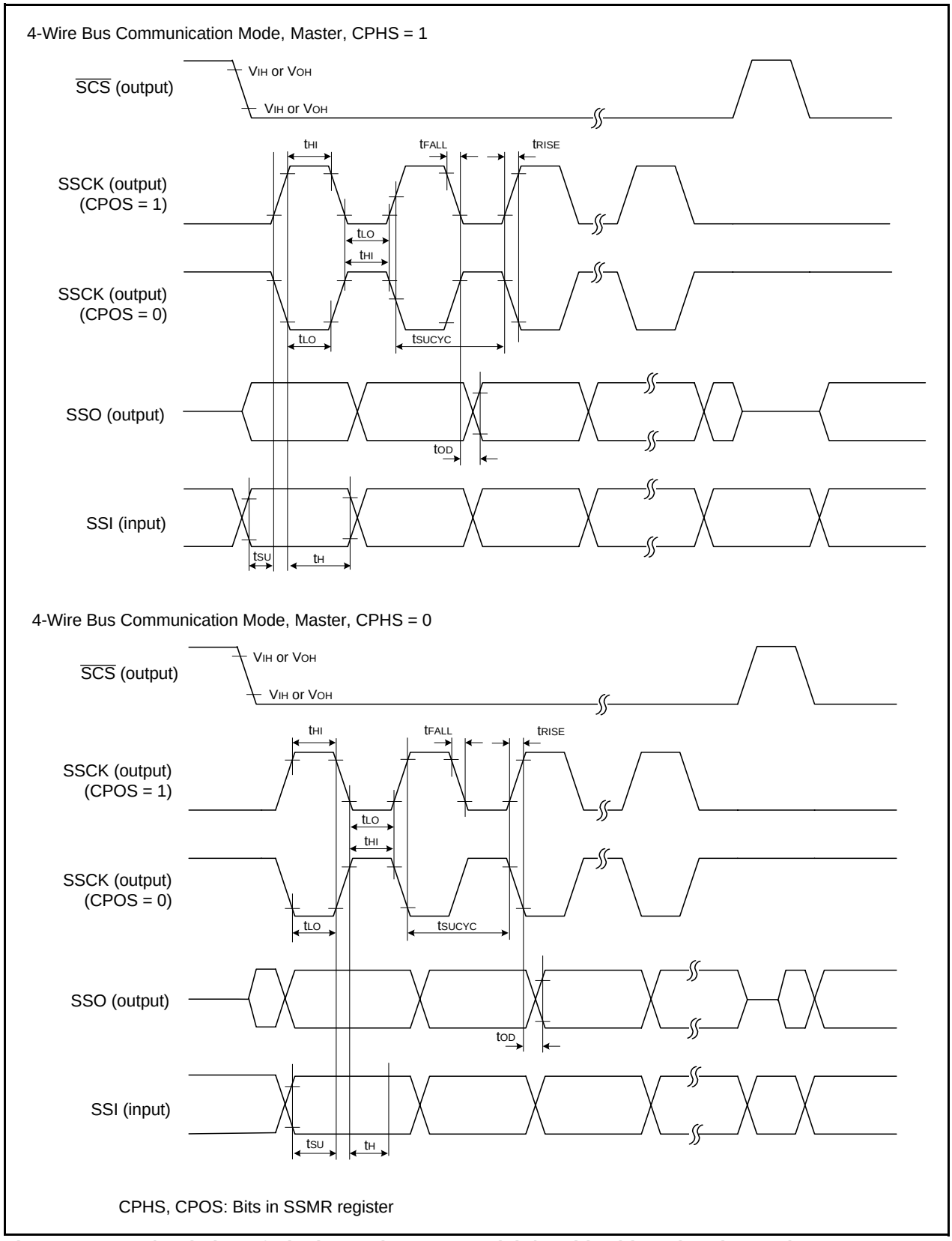


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

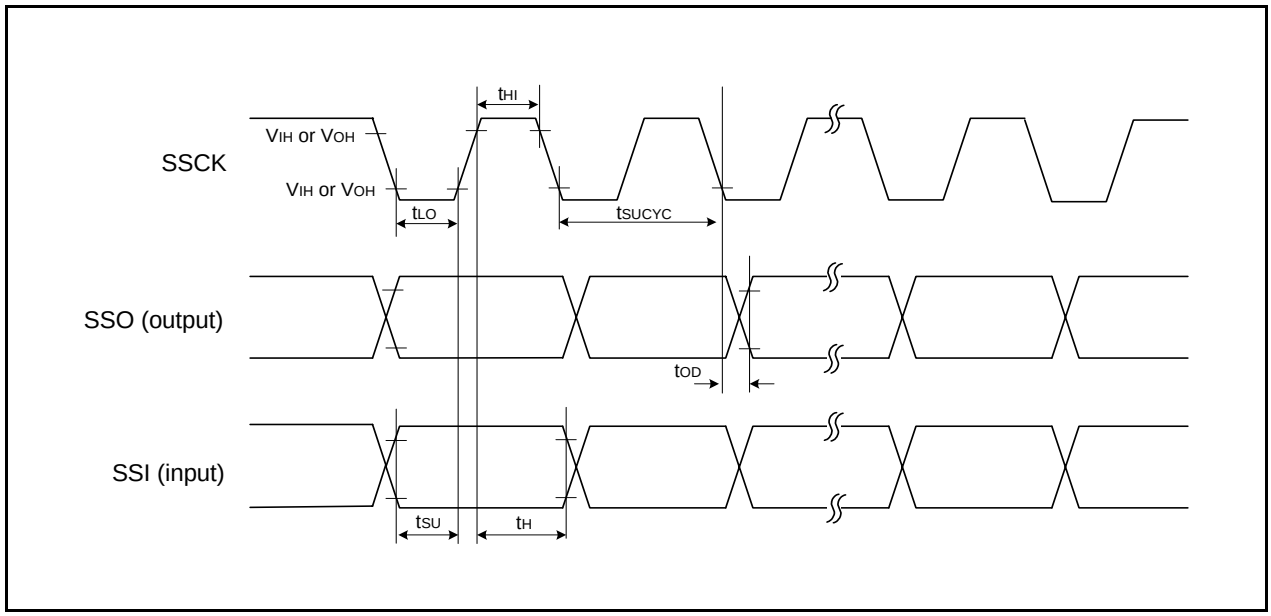


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.15 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = –5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -20 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -5 mA	V_{CC} - 2.0	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.16 Electrical Characteristics (2) [Vcc = 5 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	130	300	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.18 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

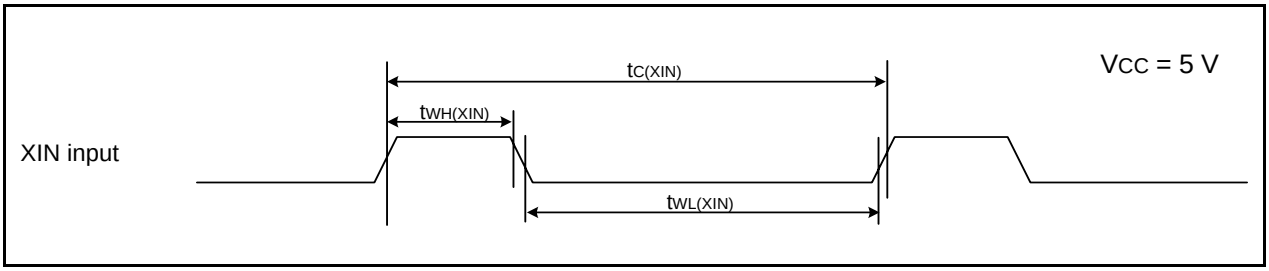


Figure 5.8 XIN Input and XCIN Input Timing Diagram when V_{CC} = 5 V

Table 5.19 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

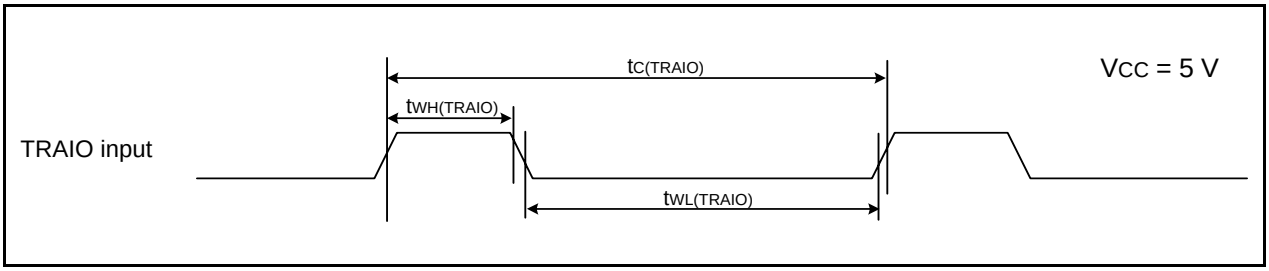


Figure 5.9 TRAIO Input Timing Diagram when V_{CC} = 5 V

5.2 J, K Version

Table 5.34 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC} + 0.3	V
V_O	Output voltage		-0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	-40 °C ≤ T_{opr} ≤ 85 °C	300	mW
		85 °C ≤ T_{opr} ≤ 125 °C	125	mW
T_{opr}	Operating ambient temperature		-40 to 85 (J version) / -40 to 125 (K version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.35 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.7	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents			–	–	10	mA
$I_{OL(avg)}$	Average output “L” current			–	–	5	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V_{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected (other than K version)	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected	–	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

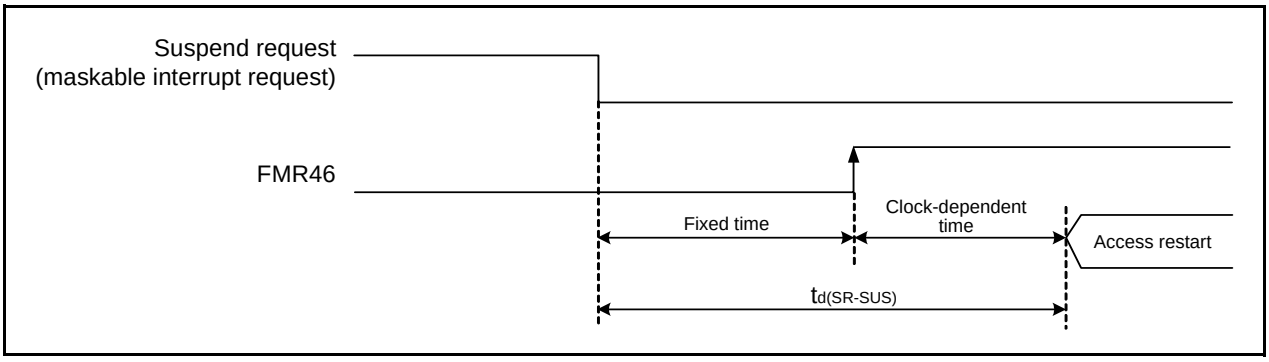


Figure 5.21 Time delay until Suspend

Table 5.39 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(2, 4)		2.70	2.85	3.0	V
$t_{d(Vdet1-A)}$	Voltage monitor 1 reset generation time(5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.70	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version).
2. Hold $V_{det2} > V_{det1}$.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.
5. Time until the voltage monitor 1 reset is generated after the voltage passes V_{det1} when V_{CC} falls. When using the digital filter, its sampling time is added to $t_{d(Vdet1-A)}$. When using the voltage monitor 1 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det1} when the power supply falls.

Table 5.40 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(2)		3.3	3.6	3.9	V
$t_{d(Vdet2-A)}$	Voltage monitor 2 reset/interrupt request generation time(3, 5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(4)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version).
2. Hold $V_{det2} > V_{det1}$.
3. Time until the voltage monitor 2 reset/interrupt request is generated after the voltage passes V_{det2}.
4. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
5. When using the digital filter, its sampling time is added to $t_{d(Vdet2-A)}$. When using the voltage monitor 2 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det2} when the power supply falls.

Table 5.45 Timing Requirements of Clock Synchronous Serial I/O with Chip Select(1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC}(2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC}(2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC}(2)
t_{SA}	SSI slave access time			–	–	$1.5t_{CYC}$ + 100	ns
t_{OR}	SSI slave out open time			–	–	$1.5t_{CYC}$ + 100	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

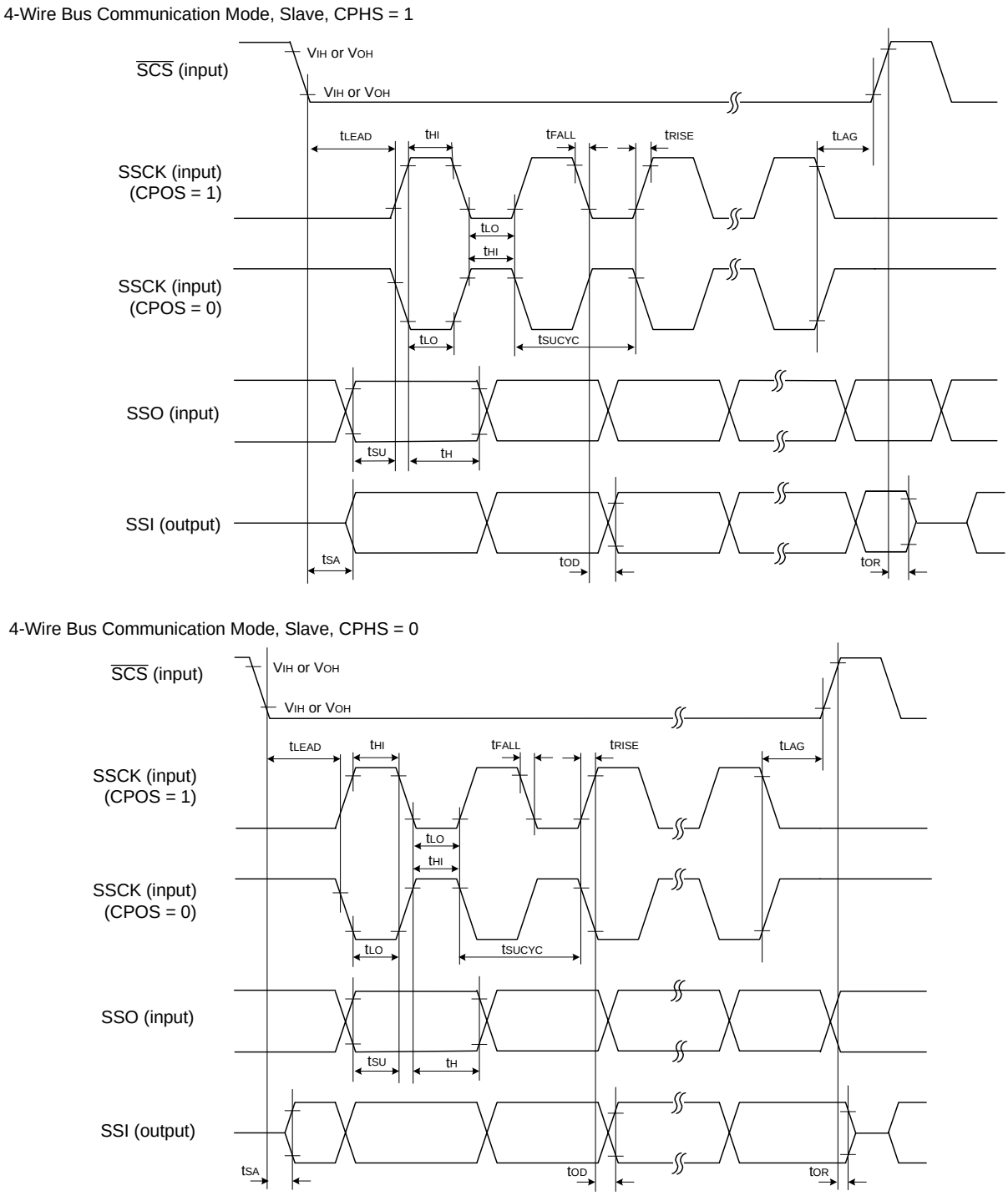


Figure 5.24 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.47 Electrical Characteristics (1) [V_{CC} = 5 V]

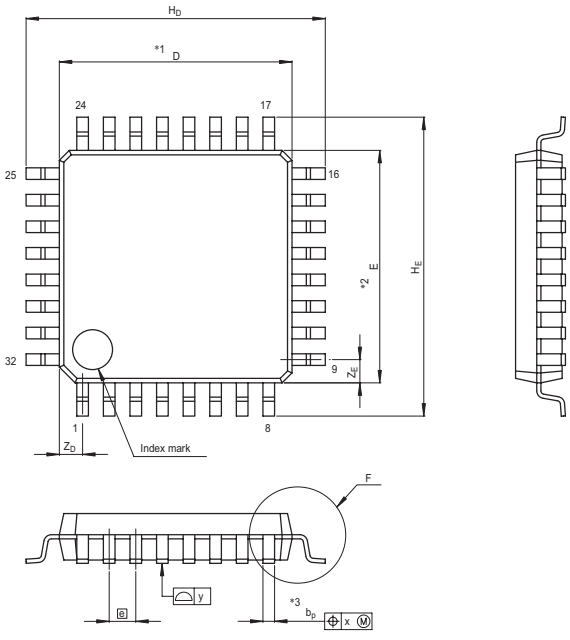
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.3	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

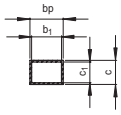
NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Package Dimensions

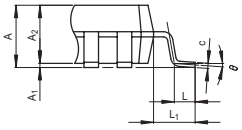
Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP32-7x7-0.80	PLQP0032GB-A	32P6U-A	0.2g





Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.32	0.37	0.42
b_1	—	0.35	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.8	—
x	—	—	0.20
y	—	—	0.10
Z_D	—	0.7	—
Z_E	—	0.7	—
L	0.3	0.5	0.7
L_1	—	1.0	—